

目次

1. Reliability Studies on MOCVD Grown AlGa _N /Ga _N HEMT on Si Substrate	1
2. 本研究に関連した発表・論文	93
[1] Normally-OFF Al ₂ O ₃ /AlGa _N /Ga _N MOS-HEMT on 8 in. Si with Low Leakage Current and High Breakdown Voltage (825V).....	93
[2] Electrical properties of Ga _N -based metal-insulator-semiconductor structures with Al ₂ O ₃ deposited by atomic layer deposition using water and ozone as the oxygen precursors	96
[3] High Drain Current Density E-Mode Al ₂ O ₃ /AlGa _N /Ga _N MOS-HEMT on Si With Enhanced Power Device Figure-of-Merit ($4 \times 10^8 \text{ V}^2 \Omega^{-1} \text{ cm}^{-2}$).....	102
[4] Evaluation of Electron Trapping Speed of AlGa _N /Ga _N HEMT With Real-Time Electroluminescence and Pulsed <i>I-V</i> Measurements.....	107
[5] Step-Stress Reliability Studies on AlGa _N /Ga _N High Electron Mobility Transistors on Silicon with Buffer Thickness Dependence.....	114
[6] Influence of Ga _N Stress on Threshold Voltage Shift in AlGa _N /Ga _N High-Electron-Mobility Transistors on Si under Off-State Electrical Bias.....	117
[7] Origin and Appearance of Defective Pits in the Gate-Drain Region during Reliability Measurements of AlGa _N /Ga _N High-Electron-Mobility Transistors on Si.....	121
[8] Characterization of InAlN/Ga _N high-electron-mobility transistors grown on Si substrate using graded layer and strain-layer superlattice.....	124
[9] Influence of the barrier composition in Ga _N /In _x Al _{1-x} N quantum wells properties.....	127
[10] Transfer-free graphene synthesis on insulating substrates via agglomeration phenomena of catalytic nickel films	132
本研究関連の新聞記事	137
教職員名簿	141